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Susan V. Stiles

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Docket: 0756-1/3637/24/96

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of

Hisashi OHTANI et al.

Serial No. 08/479,211

Filed: June 7, 1995

For: METHOD FOR MANUFACTURING)

SEMICONDUCTOR DEVICE

Art Unit: 1104

Examiner: L. Radomsky

) Date: July 8, 1996

AMENDMENT

Honorable Commissioner of Patents and Trademarks

Washington, D.C. 20231

Sir:

In response to the Office Action of March 18, 1996, please amend the subject application as follows:

In the Claims:

Please amend claim 1 as follows:

1. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon in contact with a silicon nitride film;

forming a continuous layer of a material including a catalyst capable of promoting a crystallization of silicon onto at least a portion of said semiconductor film;

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